



#### 1A STEP-DOWN CONSTANT CURRENT, HIGH EFFICIENCY LED DRIVER

## **Description**

The PAM2804 is a step-down constant current LED driver. When the input voltage down to lower than LED forward voltage, then PAM2804 run into LDO mode.

The PAM2804 supports a range of input voltages from 2.5V to 6.0V, allowing the use of a single Li+/Li-polymer cell, 3AA or 4AA cell, USB, and other standard power sources.

The FB voltage is only 0.1V to achieve high efficiency.

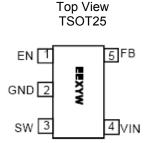
PAM2804 employ internal power switch and synchronous rectifier to minimize external part count and realize high efficiency.

During shutdown, the input is disconnected from the output and the shutdown current is less than 1µA. Other key features include undervoltage lockout to prevent deep battery discharge of the Li+ battery.

#### **Features**

- Efficiency up to 93%
- 180µA(typ) Quiescent Current
- Output Current: Up to 1A
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency
- Soft-Start
- Under-Voltage Lockout
- Short LED Protection
- Open LED Protection
- Thermal Shutdown
- 5-Pin Small TSOT25 Packages
- Pb-Free Package

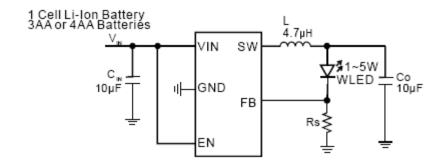
## **Pin Assignments**



## **Applications**

- 3AA or 4AA Batteries Powered Flashlight
- 1 Cell Li-Ion Battery Powered Flashlight

# **Typical Applications Circuit**



 $I_{LED} = 0.1/R_S$ 

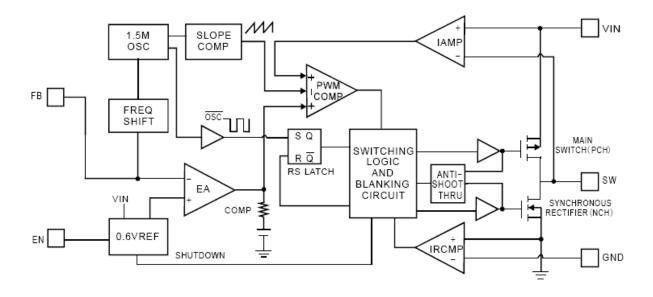




## **Pin Description**

Pin Number	Pin Name	Function	
1	EN	Enable control input. Force this pin voltage above 1.5V, enables the chip, and below 0.3V shuts down the device.	
2	GND	Ground	
3	SW	The drains of the internal main and synchronous power MOSFET.	
4	VIN	Chip main power supply pin.	
5	FB	Feedback voltage to internal error amplifier, the threshold voltage is 0.1V.	

# **Block Diagram**



# **Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

Parameter	Rating	Unit
Input Pin Voltage	-0.3 to +6.5	
EN, FB Pin Voltage	-0.3 to V <sub>IN</sub>	V
SW Pin Voltage	-0.3 to (V <sub>IN</sub> +0.3)	
Junction Temperature Range	150	
Storage Temperature Range	-65 to +150	°C
Soldering Temperature	300, 5sec	





# Recommended Operating Conditions (@TA = +25°C, unless otherwise specified.)

Parameter	Rating	Unit
Supply Voltage	2.5 to 6.0	
Operation Temperature Range	-40 to +85	°C
Junction Temperature Range	-40 to +125	

# **Thermal Information**

Parameter	Symbol	Package	Max	Unit
Thermal Resistance (Junction to Case)	$\theta_{JC}$	TSOT25 (Note 1)	130	°C/W
Thermal Resistance (Junction to Ambient)	$\theta_{JA}$	TSOT25	250	C/VV
Internal Power Dissipation	P <sub>D</sub>	TSOT25	400	mW

Note: 1. The maximum output current for TSOT25 package is limited by internal power dissipation capacity as described in Application Information herein after.

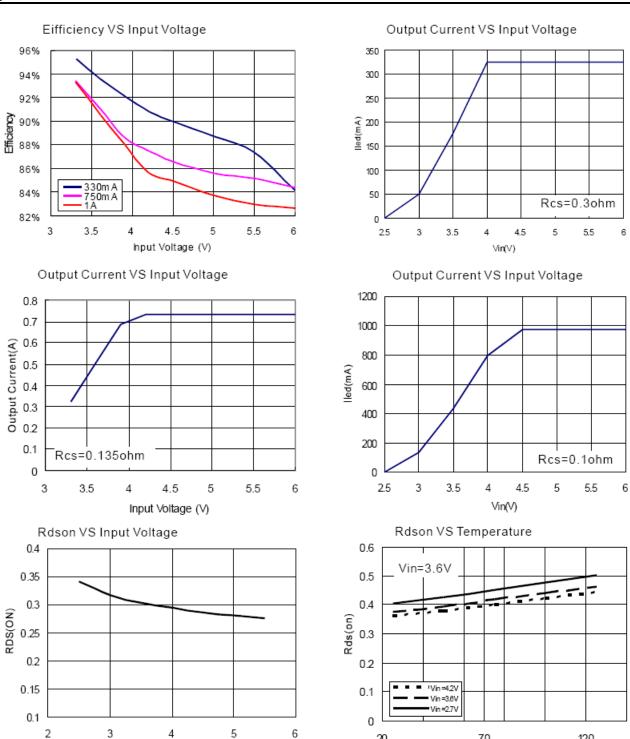
## **Electrical Characteristics**

(@ $T_A$  = +25°C,  $V_{IN}$  = 4.2V, Real WLED load, L = 4.7 $\mu$ H,  $C_{IN}$  = 10 $\mu$ F,  $C_O$  = 10 $\mu$ F, unless otherwise specified.)

Parameter	Symbol	Test	Conditions	Min	Тур	Max	Units
Input Voltage Range	V <sub>IN</sub>			2.5		6.0	V
Regulated Feedback Voltage	V <sub>FB</sub>			0.095	0.100	0.105	V
Peak Inductor Current	I <sub>PK</sub>	V <sub>IN</sub> = 5V			1.5		Α
Quiescent Current	IQ	No Load			180		μΑ
Shutdown Current	I <sub>SD</sub>	V <sub>EN</sub> = 0V				1	μΑ
Oscillator Frequency	fosc	V <sub>O</sub> = 100%		1.2	1.5	1.8	MHz
Drain Course On State Begintance	Б	L = 400 == A	P MOSFET		0.30	0.45	Ω
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	I <sub>DS</sub> = 100mA	N MOSFET		0.35	0.50	Ω
SW Leakage Current	I <sub>LSW</sub>				±0.01	1	μA
High Efficiency	η				93		%
EN Threshold High	V <sub>EH</sub>			1.5			V
EN Threshold Low	V <sub>EL</sub>					0.3	V
EN Leakage Current	I <sub>EN</sub>				±0.01		μA
Over Temperature Protection	OTP				150		°C
OTP Hysteresis	OTH				30		°C



## Typical Performance Characteristics (@T<sub>A</sub> = +25°C, L = 4.7μF, C<sub>IN</sub> = 10μF, C<sub>O</sub> = 10μF, unless otherwise specified.)



Input Voltage

120

70

Temperature(°C)

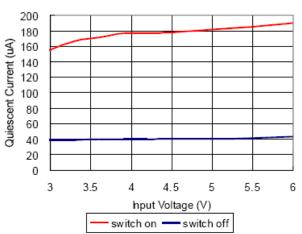
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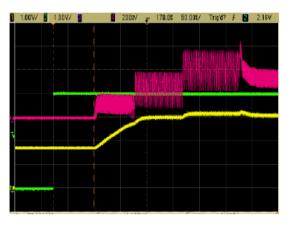


# $\textbf{Typical Performance Characteristics} \ (\texttt{cont.}) \ \textcircled{@} T_{A} = +25 \ ^{\circ}\text{C}, \ L = 4.7 \mu\text{F}, \ C_{IN} = 10 \mu\text{F}, \ C_{O} = 10 \mu\text{F}, \ unless otherwise specified.})$

# Quiescent Current Vs Input Voltage



## Start up with Enable



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## Application Information

The basic PAM2804 application circuit is shown in Page 1. External component selection is determined by the load requirement, selecting L first and then CIN and COUT.

#### Inductor Selection

For most applications, the value of the inductor will fall in the range of 1µH to 4.7µH. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V<sub>IN</sub> or V<sub>OUT</sub> also increases the ripple current as shown in equation 1. A reasonable starting point for setting ripple current is  $\Delta I_L = 400$ mA (40% of 1A).

$$\Delta I_{L} = \frac{1}{(f)(L)} V_{OUT} \left( 1 - \frac{V_{OUT}}{V_{IN}} \right)$$
 Equation (1)

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.4A rated inductor should be enough for most applications (1A + 400mA). For better efficiency, choose a low DC-resistance inductor.

### **Using Ceramic Input Output Capacitors**

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

#### **Thermal Consideration**

Thermal protection limits power dissipation in the PAM2804. When the junction temperature exceeds +150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below +120°C.

For continuous operation, the junction temperature should be maintained below +125°C. The power dissipation is defined as:

$$P_{D} = I_{O}^{2} \frac{V_{O} R_{DS(ON)H} + (V_{IN} - V_{O}) R_{DS(ON)L}}{V_{IN}} + (t_{SW} F_{S} I_{O} + I_{Q}) V_{IN}$$

lo is the step-down converter quiescent current. The term tsw is used to estimate the full load step-down converter switching losses.

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_D = I_O^2 R_{DS(ON)H} + I_Q V_{IN}$$

Since R<sub>DS(ON)</sub>, quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where  $T_{J(MAX)}$  is the maximum allowable junction temperature +125°C.  $T_A$  is the ambient temperature and  $\theta_{JA}$  is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance θ<sub>JA</sub> of TSOT25 package is 250°C/W. The maximum power dissipation at T<sub>A</sub> = +25°C can be calculated by following formula:

$$P_D = (125^{\circ}C - 25^{\circ}C)/250^{\circ}C/W = 0.4W$$

6 of 10 PAM2804 January 2013 www.diodes.com © Diodes Incorporated Document number: DSxxxxx Rev. 2 - 0



## **Application Information**

#### **Setting the Output Current**

The internal feedback(FB) voltage is 0.1V (Typical). The output current is calculated as below:

$$I_{1FD} = 0.1/R_{S}$$

The output Current is given by the following table.

$R_S(\Omega)$	I <sub>LED</sub> (mA)	
0.286	350	
0.143	700	
0.1	1000	

As the input voltage approaches the LED forward voltage, the PAM2804 turns the P-Chan nel transistor continuously on. In this mode the Voltage drop on LED is equal to the input voltage minus the voltage drop across the P-Channel transistor, Inductor and current resistor:

$$V_{LEDDROP} = V_{IN} - ILED(R_{DS(ON)} + R_L + R_S)$$

where R<sub>DS(ON)</sub> = P-Channel switch ON resistance, ILED = LED current, R<sub>L</sub> = Inductor DC Resistance, R<sub>S</sub> = Inductor DC Resistance.

#### **Thermal Shutdown**

When the die temperature exceeds +150°C, a reset occurs and the reset remains until the temperature decrease to +120°C, at which time the circuit can be restarted.

#### **PCB Layout Check List**

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the PAM2804. These items are also illustrated graphically in Figure 1. Check the following in your layout:

- 1. The power traces, consisting of the GND trace, the SW trace and the VIN trace should be kept short, direct and wide.
- 2. Does the V<sub>FB</sub> pin connect directly to the current sense resistor? The current sense resistor to GND trace should be kept short, direct and wide.

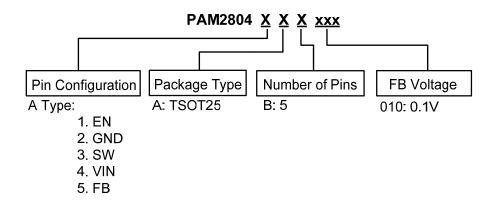
7 of 10

- 3. Does the (+) plate of C<sub>IN</sub> connect to V<sub>IN</sub> as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
- 4. Keep the switching node, SW, away from the sensitive VFB node.
- 5. Keep the (-) plates of C<sub>IN</sub> and C<sub>OUT</sub> as close as possible.



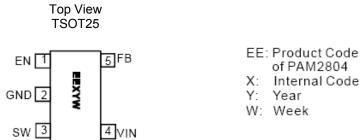


# **Ordering Information**



Part Number	Marking	Package Type	Standard Package
PAM2804AAB010	Refer to Marking Information Below	TSOT25	3000 Units/Tape&Reel

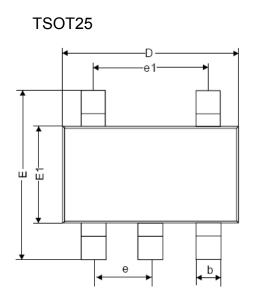
# **Marking Information**

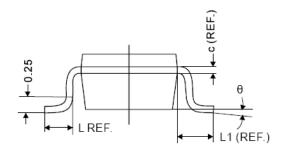


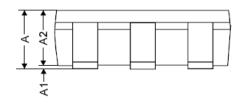




# Package Outline Dimensions (All dimensions in mm.)







REF.	Millimeter		
KET.	Min	Max	
Α	1.10 N	ΛΑΧ	
A1	0	0.10	
A2	0.70	1	
С	0.12 F	REF.	
D	2.70	3.10	
E	2.60	3.00	
E1	1.40	1.80	
L	0.45 REF.		
L1	0.60 REF.		
θ	0°	10°	
b	0.30	0.50	
е	0.95 REF.		
e1	1.90 REF.		





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